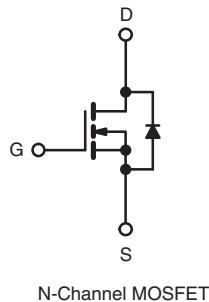
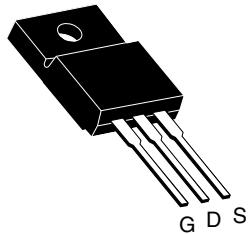


E Series Power MOSFET

PRODUCT SUMMARY	
V_{DS} (V) at T_J max.	700
$R_{DS(on)}$ max. at 25 °C (Ω)	$V_{GS} = 10$ V 0.18
Q_g max. (nC)	110
Q_{gs} (nC)	15
Q_{gd} (nC)	32
Configuration	Single

TO-220 FULLPAK


ORDERING INFORMATION

Package	TO-220 FULLPAK
Lead (Pb)-free	SiHF22N65E-E3
Lead (Pb)-free and Halogen-free	SiHF22N65E-GE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	650	V
Gate-Source Voltage	V_{GS}	± 30	
Continuous Drain Current ($T_J = 150$ °C)	V_{GS} at 10 V	22	A
		14	
Pulsed Drain Current ^a	I_{DM}	56	
Linear Derating Factor		1.8	W/°C
Single Pulse Avalanche Energy ^b	E_{AS}	691	mJ
Maximum Power Dissipation	P_D	35	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	°C
Drain-Source Voltage Slope	$T_J = 125$ °C	70	V/ns
Reverse Diode dV/dt ^d		26	
Soldering Recommendations (Peak Temperature) ^c	for 10 s	300	°C

Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50$ V, starting $T_J = 25$ °C, $L = 28.2$ mH, $R_g = 25$ Ω, $I_{AS} = 7$ A.
- 1.6 mm from case.
- $I_{SD} \leq I_D$, $dI/dt = 100$ A/μs, starting $T_J = 25$ °C.


RoHS*
Available

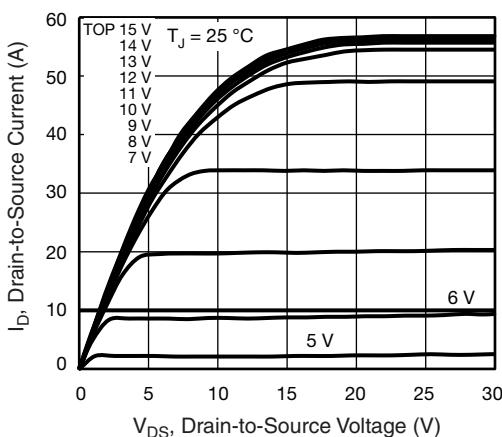
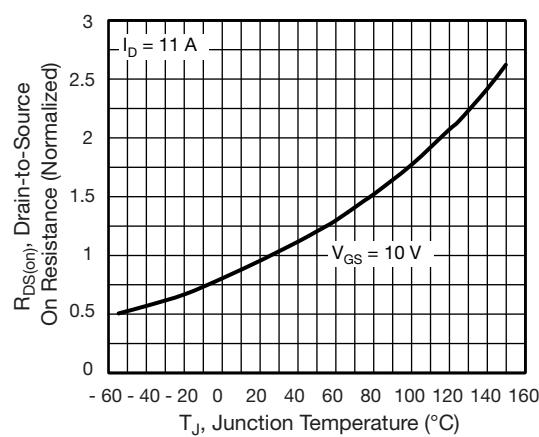
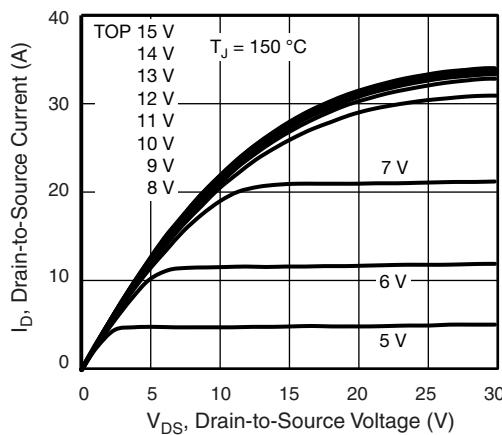
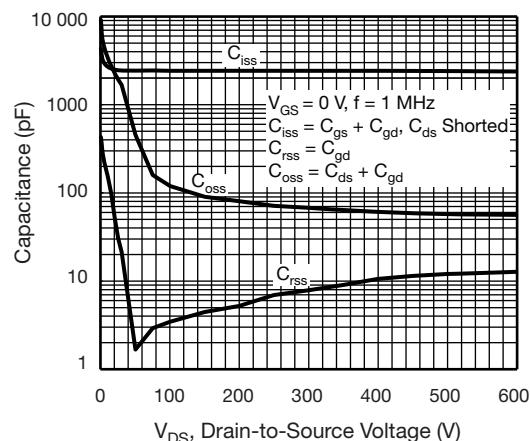
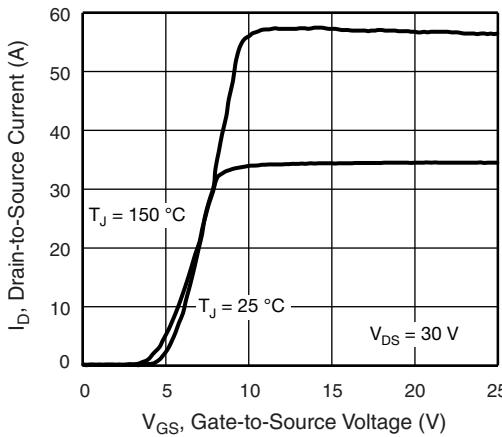
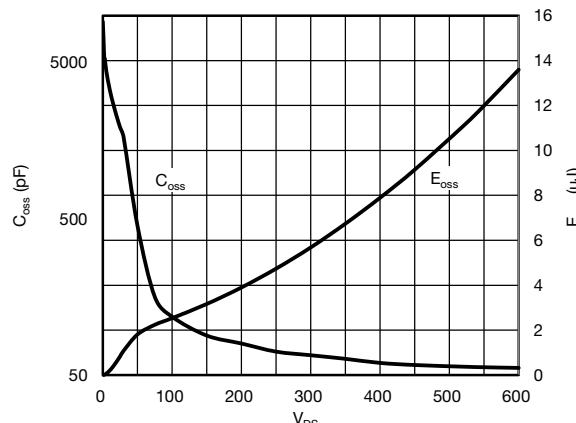
**HALOGEN
FREE**
Available

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	65	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	3.6	°C/W

SPECIFICATIONS ($T_J = 25$ °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0$ V, $I_D = 250$ μA		650	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, $I_D = 1$ mA		-	0.74	-	V/°C
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250$ μA		2	-	4	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20$ V		-	-	± 100	nA
		$V_{GS} = \pm 30$ V		-	-	± 1	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 650$ V, $V_{GS} = 0$ V		-	-	1	
		$V_{DS} = 520$ V, $V_{GS} = 0$ V, $T_J = 125$ °C		-	-	10	μA
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10$ V	$I_D = 11$ A	-	0.15	0.18	Ω
Forward Transconductance	g_{fs}	$V_{DS} = 8$ V, $I_D = 5$ A		-	6.7	-	S
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0$ V, $V_{DS} = 100$ V, $f = 1$ MHz		-	2415	-	pF
Output Capacitance	C_{oss}			-	118	-	
Reverse Transfer Capacitance	C_{rss}			-	4	-	
Effective Output Capacitance, Energy Related ^a	$C_{o(er)}$	$V_{DS} = 0$ V to 520 V, $V_{GS} = 0$ V		-	89	-	
Effective Output Capacitance, Time Related ^b	$C_{o(tr)}$			-	307	-	
Total Gate Charge	Q_g			-	73	110	nC
Gate-Source Charge	Q_{gs}	$V_{GS} = 10$ V	$I_D = 11$ A, $V_{DS} = 520$ V	-	15	-	
Gate-Drain Charge	Q_{gd}			-	32	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 520$ V, $I_D = 11$ A, $V_{GS} = 10$ V, $R_g = 9.1$ Ω		-	22	45	ns
Rise Time	t_r			-	33	66	
Turn-Off Delay Time	$t_{d(off)}$			-	73	110	
Fall Time	t_f			-	38	76	
Gate Input Resistance	R_g	$f = 1$ MHz, open drain		-	0.64	-	Ω
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	22	A
Pulsed Diode Forward Current	I_{SM}			-	-	56	
Diode Forward Voltage	V_{SD}	$T_J = 25$ °C, $I_S = 11$ A, $V_{GS} = 0$ V		-	-	1.2	V
Reverse Recovery Time	t_{rr}	$T_J = 25$ °C, $I_F = I_S = 11$ A, $dI/dt = 100$ A/μs, $V_R = 400$ V		-	400	-	ns
Reverse Recovery Charge	Q_{rr}			-	5.9	-	μC
Reverse Recovery Current	I_{RRM}			-	20	-	A

Notes

a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS} .
b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS} .

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics

Fig. 4 - Normalized On-Resistance vs. Temperature

Fig. 2 - Typical Output Characteristics

Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

Fig. 3 - Typical Transfer Characteristics

Fig. 6 - C_{oss} and E_{oss} vs. V_{DS}

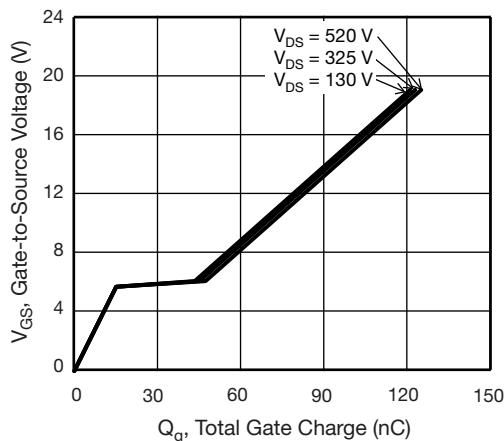


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

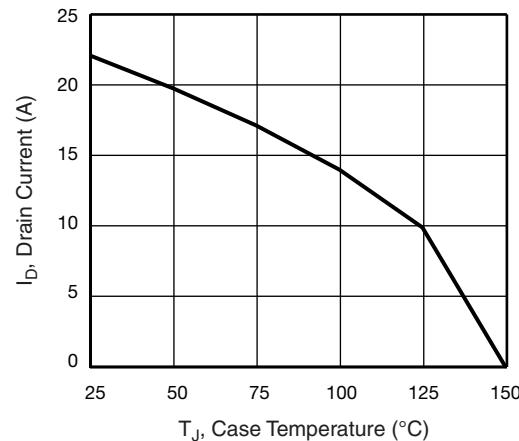


Fig. 10 - Maximum Drain Current vs. Case Temperature

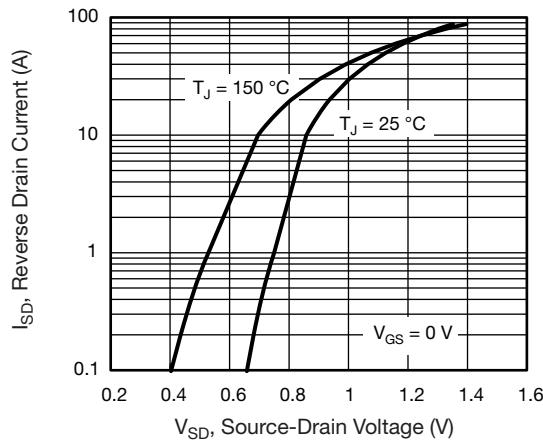


Fig. 8 - Typical Source-Drain Diode Forward Voltage

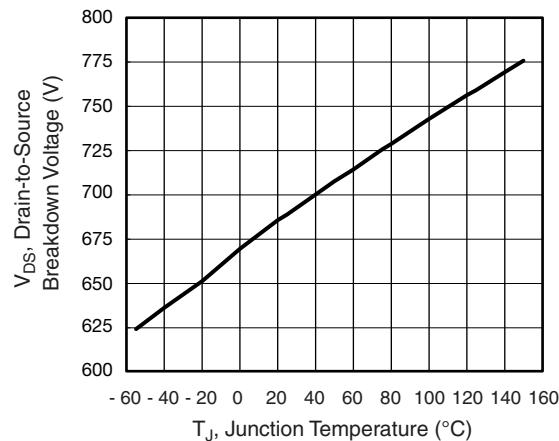


Fig. 11 - Temperature vs. Drain-to-Source Voltage

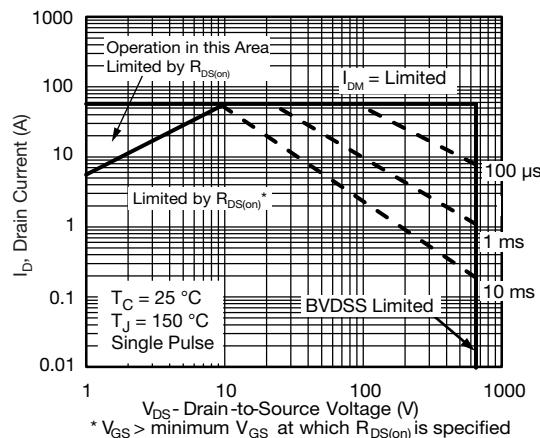


Fig. 9 - Maximum Safe Operating Area

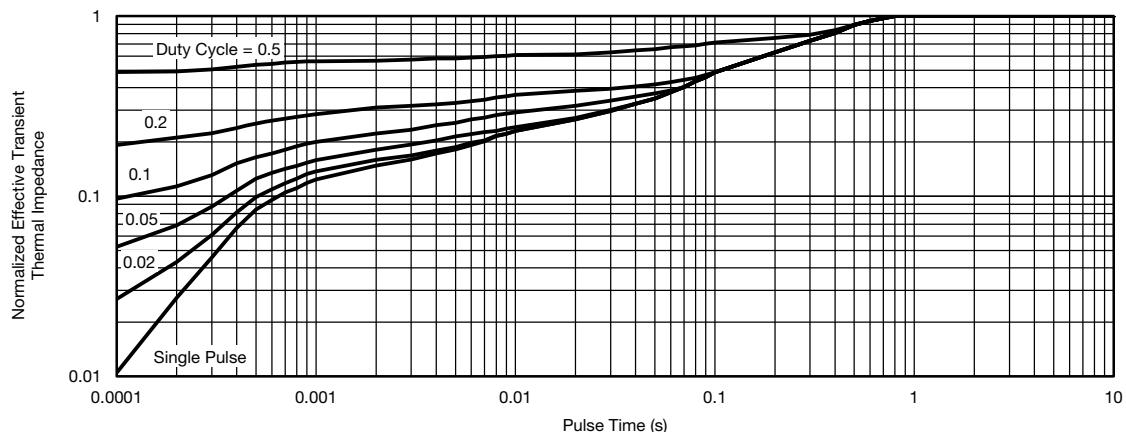


Fig. 12 - Normalized Thermal Transient Impedance, Junction-to-Case

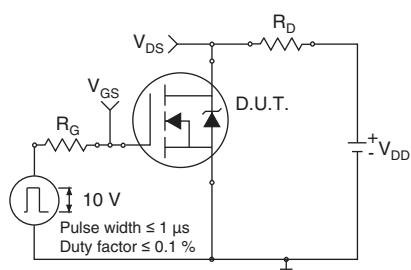


Fig. 13 - Switching Time Test Circuit

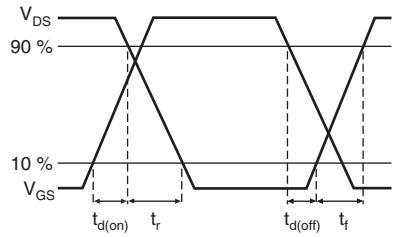


Fig. 14 - Switching Time Waveforms

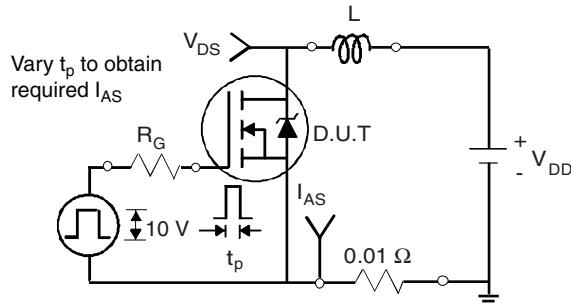


Fig. 15 - Unclamped Inductive Test Circuit

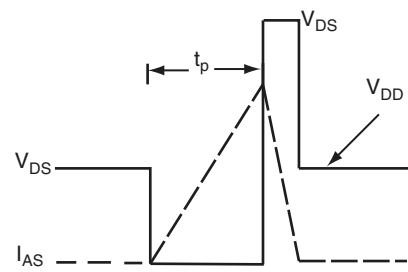


Fig. 16 - Unclamped Inductive Waveforms

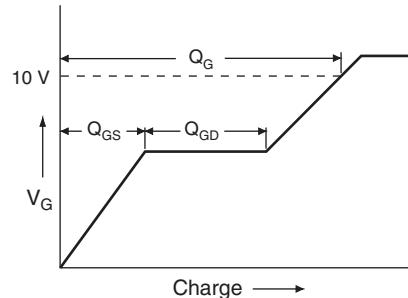


Fig. 17 - Basic Gate Charge Waveform

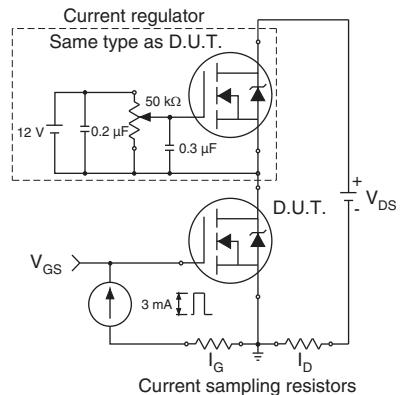


Fig. 18 - Gate Charge Test Circuit

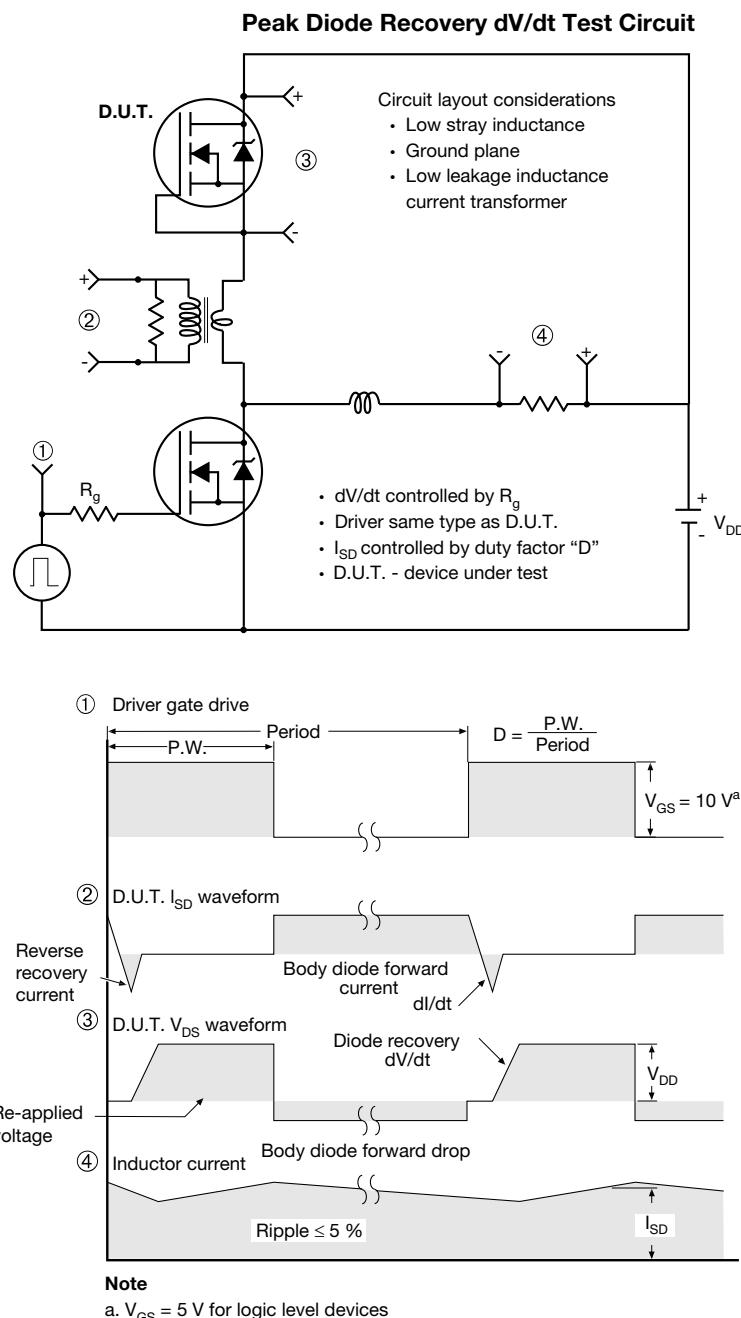
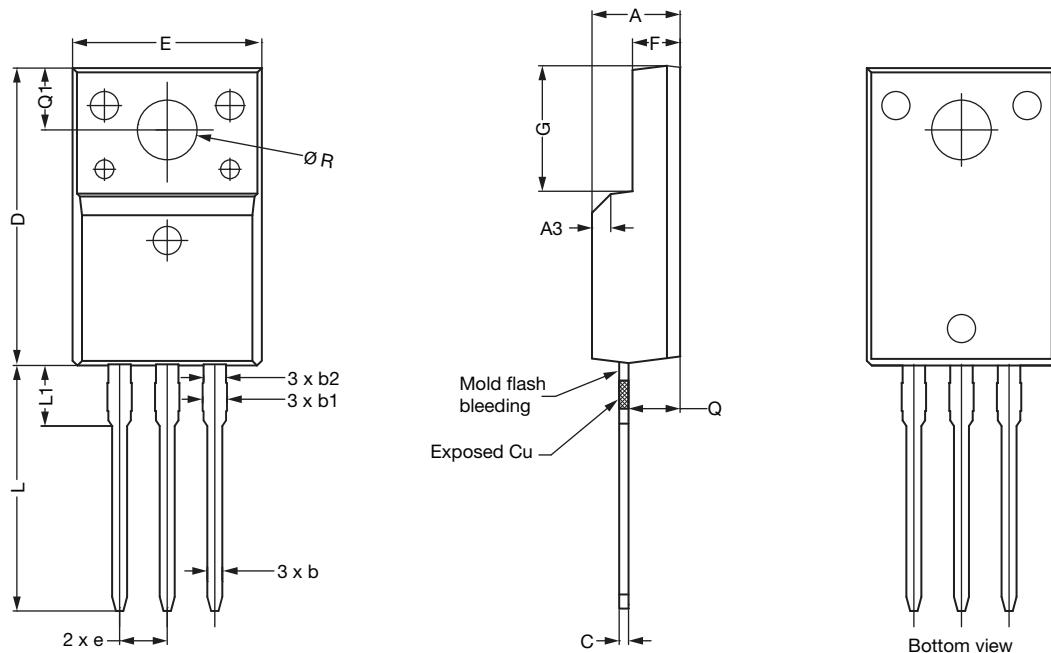


Fig. 19 - For N-Channel

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TO-220 FULLPAK (High Voltage)

OPTION 1: FACILITY CODE = 9

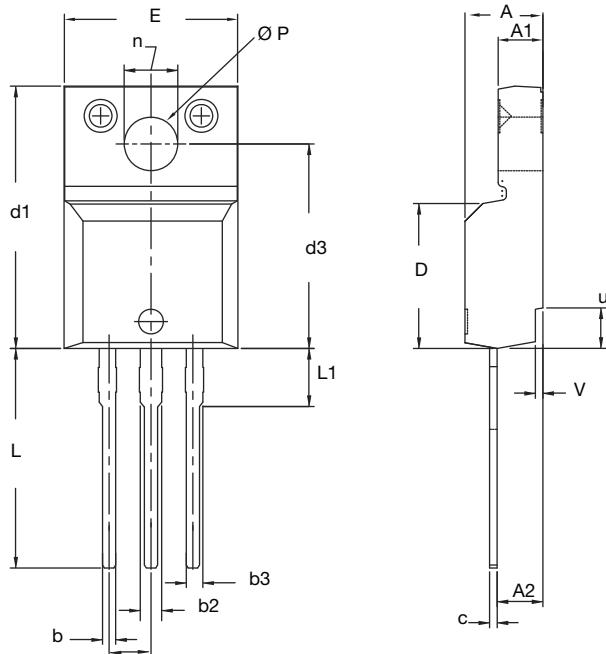


MILLIMETERS			
DIM.	MIN.	NOM.	MAX.
A	4.60	4.70	4.80
b	0.70	0.80	0.91
b1	1.20	1.30	1.47
b2	1.10	1.20	1.30
C	0.45	0.50	0.63
D	15.80	15.87	15.97
e	2.54 BSC		
E	10.00	10.10	10.30
F	2.44	2.54	2.64
G	6.50	6.70	6.90
L	12.90	13.10	13.30
L1	3.13	3.23	3.33
Q	2.65	2.75	2.85
Q1	3.20	3.30	3.40
Ø R	3.08	3.18	3.28

Notes

1. To be used only for process drawing
2. These dimensions apply to all TO-220 FULLPAK leadframe versions 3 leads
3. All critical dimensions should C meet $C_{pk} > 1.33$
4. All dimensions include burrs and plating thickness
5. No chipping or package damage
6. Facility code will be the 1st character located at the 2nd row of the unit marking

OPTION 2: FACILITY CODE = Y



	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
A	4.570	4.830	0.180	0.190
A1	2.570	2.830	0.101	0.111
A2	2.510	2.850	0.099	0.112
b	0.622	0.890	0.024	0.035
b2	1.229	1.400	0.048	0.055
b3	1.229	1.400	0.048	0.055
c	0.440	0.629	0.017	0.025
D	8.650	9.800	0.341	0.386
d1	15.88	16.120	0.622	0.635
d3	12.300	12.920	0.484	0.509
E	10.360	10.630	0.408	0.419
e	2.54 BSC		0.100 BSC	
L	13.200	13.730	0.520	0.541
L1	3.100	3.500	0.122	0.138
n	6.050	6.150	0.238	0.242
$\emptyset P$	3.050	3.450	0.120	0.136
u	2.400	2.500	0.094	0.098
V	0.400	0.500	0.016	0.020

ECN: E19-0180-Rev. D, 08-Apr-2019
 DWG: 5972

Notes

1. To be used only for process drawing
2. These dimensions apply to all TO-220 FULLPAK leadframe versions 3 leads
3. All critical dimensions should C meet $C_{pk} > 1.33$
4. All dimensions include burrs and plating thickness
5. No chipping or package damage
6. Facility code will be the 1st character located at the 2nd row of the unit marking

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